2SJ502



Ultrahigh-Speed Switching Applications

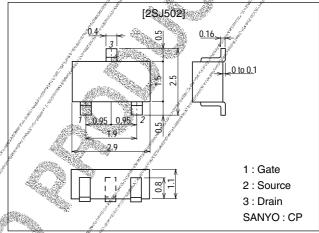
Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 4V drive.

Package Dimensions

unit:mm

2091A



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Drain-to-Source Voltage	Vøss	-30	V
Gate-to-Source Voltage	VGSS /	±20	V
Drain Current (DC)	//b	-0.5	Α
Drain Current (Pulse)	I _{DP} PW≤10µs, duty cycle≤1%	-2.0	Α
Allowable Power Dissipation	y Po	0.25	W
Channel Temperature	(Teh	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol Conditions	Conditions	Ratings			Unit
raiametei		Conditions	min	typ	max	Onit
Drain-to-Source Breakdown Voltage	¥(BR)DSS	Ip=-1mA, V _{GS} =0	-30			V
Zero-Gate Voltage Drain, Current		V _{DS} =-30V, V _{GS} =0			-10	μΑ
Gate-to-Source Leakage Current	I _{G\$\$.}	V _{GS} =±16V, V _{DS} =0			±10	μA
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-1.0		-2.5	V
Forward Transfer Admittance	/ lyfs l	V _{DS} =-10V, I _D =-300mA	300	800		mS
Static Drain-te-Source On State Resistance	PDS(on)1	I _D =-300mA, V _{GS} =-10V		360	600	mΩ
Static Diani-to-Source Off State nesistance	R _{DS(on)} 2	I _D =-300mA, V _{GS} =-4V		690	970	mΩ

Marking : FM

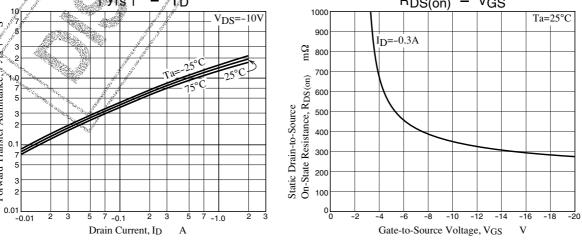
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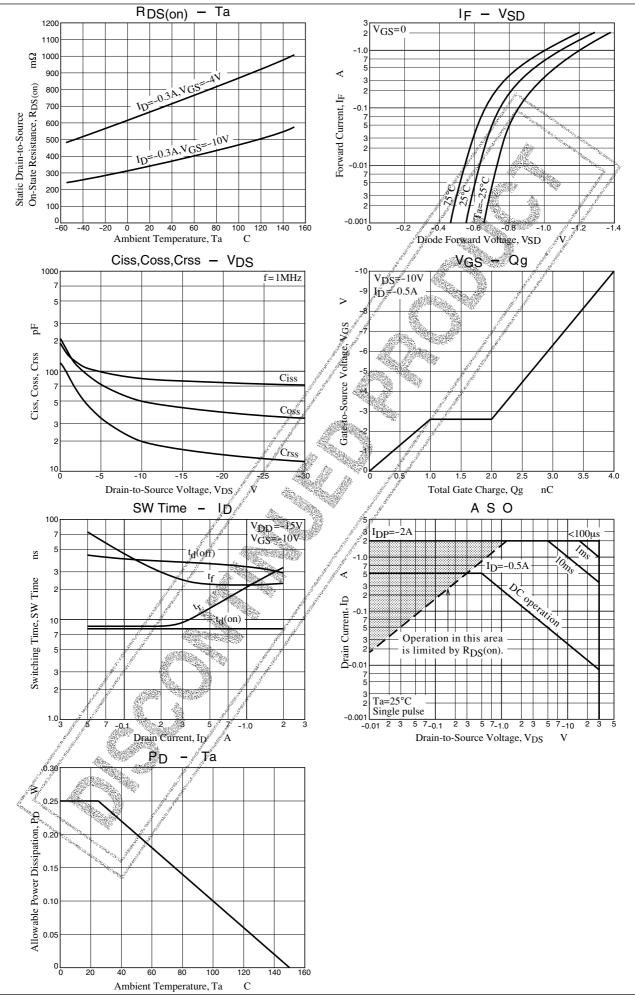
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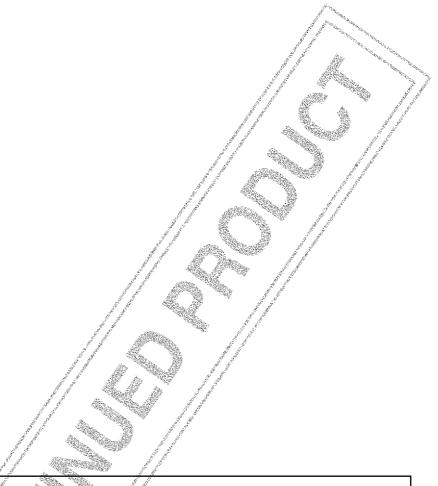
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Parameter	Symbol	Conditions	Ratings			Unit
Parameter			min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		90		pF
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz	di s	50		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-10V, f=1MHz	1	20		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit	A STATE OF THE STA	. 8		ns
Rise Time	t _r	See specified Test Circuit	J.	*1,0	and the same of th	ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit		40	Sept Maria Sept.	ns
Fall Time	t _f	See specified Test Circuit		25	1000	ns
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-10V, I _D =-500mA	- A-2000 A	4	A STATE OF THE STA	nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-10V, I _D =-500mA		1	and the second	nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-10V, I _D =-500mA	W.	1	the time and the	nC
Diode Forward Voltage	V _{SD}	I _S =-500mA, V _{GS} =0	10000	-0.93	<i>-</i> 1.5	V
Switching Time Test Circuit					ja th	

V_{DD=}—15V VIN 0V _10V ID=-300mA RL=50Ω VIN PW=10μs D.C.≤1% ⊸ Vout $\stackrel{>}{\geqslant}_{50\Omega}$ 2SJ502 P.G (🔟 S ID - VDS ID - VGS -0.6 V_{DS} =-10V -6.0V -0.5 Drain Current, ID Drain Current, ID 3.0V -0.8 -0.6 -0.4 -0.2 -0.2 -0.3 -0.4 -0.5 -0.6 -0.7 Drain-to-Source Voltage, Vps -0.9 -1.0 -4.0 Gate-to-Source Voltage, V_{GS} | yts | RDS(on) - VGS 1000 Ta=25°C $V_{\overline{DS}} = -10V$ 900 I_D=-0.3A g 800 Forward Transfer Admittance, FYfs.







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